

### **Amendments to the Claims**

This listing of claims will replace the originally filed claims in the application.

#### **Listing of Claims:**

Claims 1 – 18 (cancelled)

Claim 19 (new): A method for forming a MSiON or MSiO dielectric film comprising the steps of:

- a) vaporizing a metal source (M) to form a vaporized metal source;
- b) feeding a plurality of precursors to a deposition device, wherein said precursors comprise said vaporized metal source, a silicon source, an oxygen source, and a nitrogen source if MSiON is desired ; and
- c) forming a dielectric film, wherein said dielectric film is formed with the desired final composition absent a post deposition step.

Claim 20 (new): A method for forming a MSiN metallic film comprising the steps of:

- a) vaporizing a metal source to form a vaporized metal source;
- b) feeding a plurality of precursors to a deposition device, wherein said precursors comprise said vaporized metal source, a silicon source, and a nitrogen source; and
- c) forming a metallic film, wherein said metallic film is formed with the desired final composition absent a post deposition step.

Claim 21 (new): The method of claim 19, wherein said silicon source comprises a molecular structure absent carbon and/or a molecular structure absent chlorine.

Claim 22 (new): The method of claim 19, wherein said silicon source is in vapor phase.

Claim 23 (new): The method of claim 19, wherein said silicon source has a vapor pressure of at least about 50 torr at 20°C.

Claim 24 (new): The method of claim 19, wherein said silicon source is selected from the group comprising:

- a) disiloxane;
- b) trisilylamine;
- c) disilylamine;

- d) silylamine;
- e) tridisilylamine;
- f) aminodisilylamine;
- g) tetrasilyldiamine;
- h) disilane;
- i) derivatives of disilane and/or trisilane; and
- j) mixtures thereof.

**Claim 25 (new):** The method of claim 19, wherein said oxygen source comprises a molecular structure absent carbon and/or a molecular structure absent chlorine.

**Claim 26 (new):** The method of claim 19, wherein said oxygen source is selected from the group comprising:

- a) oxygen;
- b) nitrous oxide;
- c) ozone;
- d) disiloxane; and
- e) mixtures thereof.

**Claim 27 (new):** The method of claim 19, wherein said nitrogen source comprises a molecular structure absent carbon and/or a molecular structure absent chlorine.

**Claim 28 (new):** The method of claim 19, wherein said nitrogen source is the same as said metal source, said silicon source and/or said oxygen source.

**Claim 29 (new):** The method of claim 19, wherein said nitrogen source is ammonia.

**Claim 30 (new):** The method of claim 10, wherein said metal source is selected from the group consisting of:

- a) a dialkylamino; and/or
- b) alkoxy ligands.

**Claim 31 (new):** The method of claim 19, wherein said metal source is an inorganic compound selected from the group consisting of:

- a) hafnium (Hf);
- b) zirconium (Zr);
- c) titanium (Ti);

- d) niobium (Nb);
- e) tantalum (Ta);
- f) scandium (Sc);
- g) yttrium (Y);
- h) lanthanum (La);
- i) gadolinium (Gd);
- j) europium (Eu);
- k) praseodymium (Pr) or any another lanthanide (Ln); and
- l) mixtures thereof.

Claim 32 (new): The method of claim 19, wherein the amounts of said metal source and said silicon source in said desired final composition of said dielectric film are controlled independently.

Claim 33 (new): The method of claim 19, wherein said dielectric film is completed by using a chemical vapor deposition process.

Claim 34 (new): The method of claim 19, wherein said dielectric film step is completed by using an atomic layer deposition process.

Claim 35 (new): A MSiON or a MSiO dielectric film obtained in accordance with the process of claim 19.

Claim 36 (new): A MSiN metallic film obtained in accordance with the process of claim 19.